Product Summary

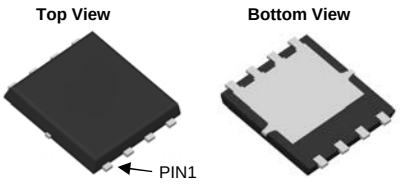
- V_{DSS}=30V, I_D=180A
- $R_{DS(ON)_Typ}$=1.2mΩ (@V_{GS}=10V)
- $R_{DS(ON)_Typ}$=1.7mΩ (@V_{GS}=4.5V)
- $V_{GS(th)_Typ}$=1.4V

Features

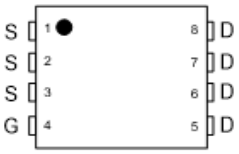
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested
- 100% ΔVds Tested
- Halogen-free; RoHS-compliant

Applications

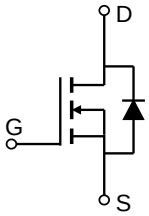
- Load Switch
- PWM Application
- Power Management



PDFN5X6-8L



Pin Assignment



Schematic Diagram

Absolute Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{DS}	Drain-to-Source Voltage		30	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25°C	180	A
		T_C = 100°C	108	
I_{DM}	Pulsed Drain Current (1)		720	A
E_{AS}	Single Pulsed Avalanche Energy (2)		272	mJ
P_D	Power Dissipation	T_C = 25°C	83	W
$R_{θJC}$	Thermal Resistance, Junction to Case		1.5	°C/W
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 24V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	1.1	1.4	2.2	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(3)	V_{GS} = 10V, I_D = 20A	-	1.2	1.5	mΩ
		V_{GS} = 4.5, I_D = 15A	-	1.7	2.4	mΩ
Dynamic Characteristics						
R_g	Gate Resistance	f = 1MHz	-	2.2	-	Ω
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 15V, f = 1MHz	-	3177	-	pF
C_{oss}	Output Capacitance		-	1756	-	pF
C_{rss}	Reverse Transfer Capacitance		-	112	-	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V, V_{DS} = 15V, I_D = 30A	-	44	-	nC
Q_{gs}	Gate Source Charge		-	9.0	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	6.0	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} = 15V, I_D= 30A, R_{GEN} = 3Ω	-	17	-	ns
t_r	Turn-On Rise Time		-	5	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	52	-	ns
t_f	Turn-Off Fall Time		-	12	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	180	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	720	A
V_{SD}	Body Diode Forward Voltage	V_{GS} = 0V, I_S = 30A	-		1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 30A, di/dt = 100A/us	-	82	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	36	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

2. E_{AS} condition: Starting T_J=25C, V_{DD}=30V, V_{GS}=10V, R_G=25ohm, L=0.5mH, I_{AS}=33A, V_{DD}=0V during time in avalanche.

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

Test Circuit

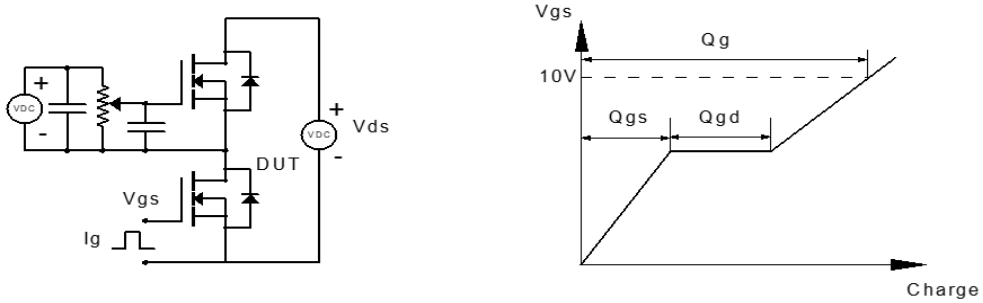


Figure 1: Gate Charge Test Circuit & Waveform

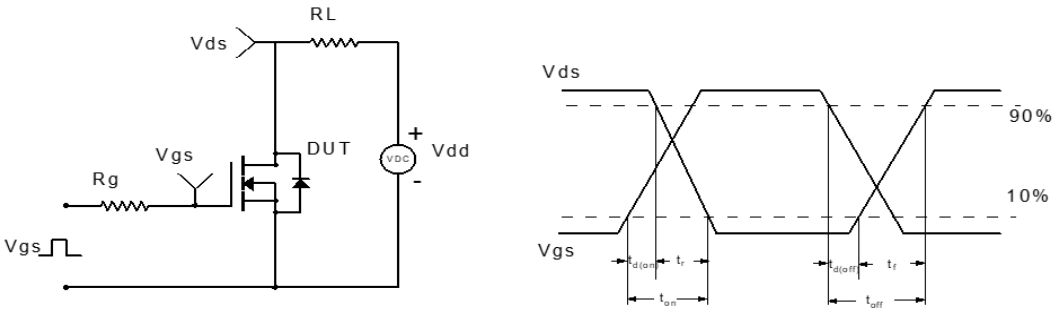


Figure 2: Resistive Switching Test Circuit & Waveform

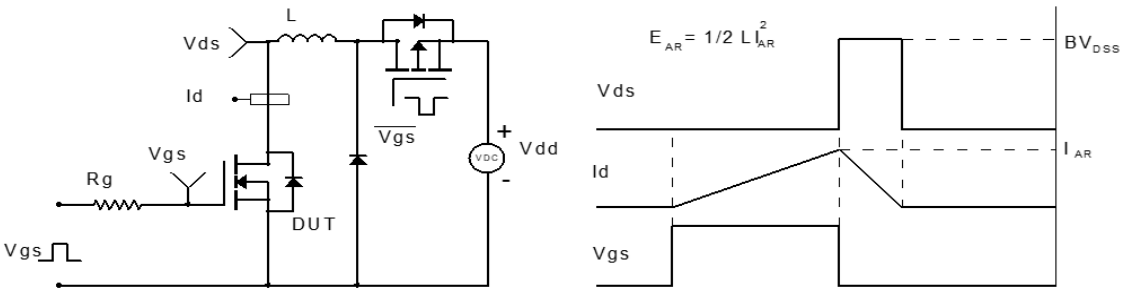


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

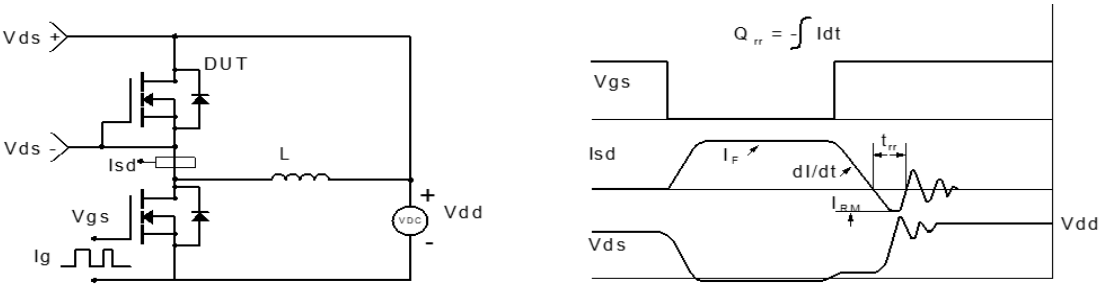
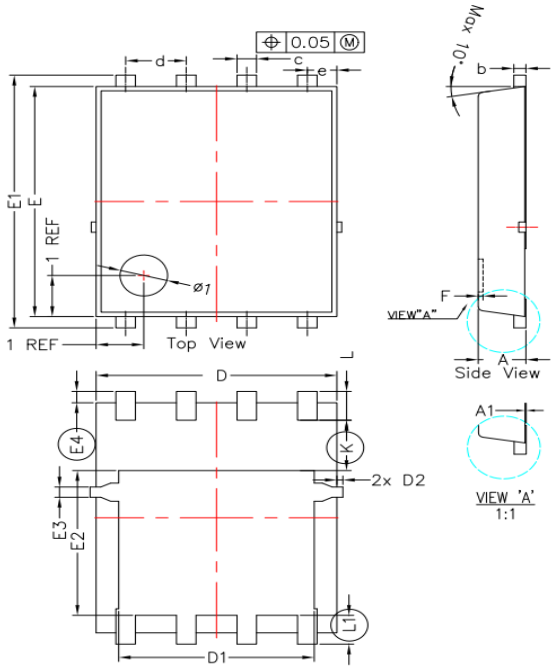


Figure 4: Diode Recovery Test Circuit & Waveform

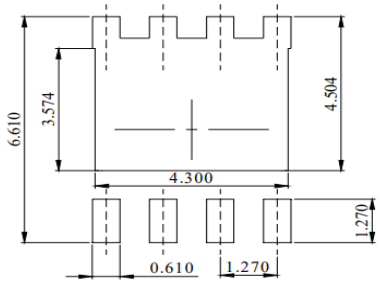
Package Mechanical Data(PDFN5X6-8L)

Package Outline



SYMBOLS	DIMENSION IN MM			DIMENSION IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
*A	0.900	1.000	1.150	0.035	0.039	0.045
A1	0.000	---	0.050	0.000	----	0.002
b	0.246	0.254	0.350	0.010	0.010	0.014
*C	0.310	0.410	0.510	0.012	0.016	0.020
d		1.27BSC			0.050BSC	
*D	4.950	5.050	5.150	0.195	0.199	0.203
D1	4.000	4.100	4.200	0.157	0.161	0.165
*D2		0.125REF			0.005REF	
e		0.62BSC			0.024BSC	
*E	5.500	5.600	5.700	0.217	0.220	0.224
*E1	6.050	6.150	6.250	0.238	0.242	0.246
E2	3.425	3.525	3.625	0.135	0.139	0.143
E3		0.250REF			0.010REF	
* E4		0.275REF			0.011REF	
F	-	-	0.100	-	-	0.004
*L	0.500	0.600	0.700	0.02	0.02	0.03
L1	0.600	0.700	0.800	0.02	0.03	0.03
K		1.225REF			0.05REF	

Recommended Soldering Footprint



DIMENSIONS:MILLIMETERS